

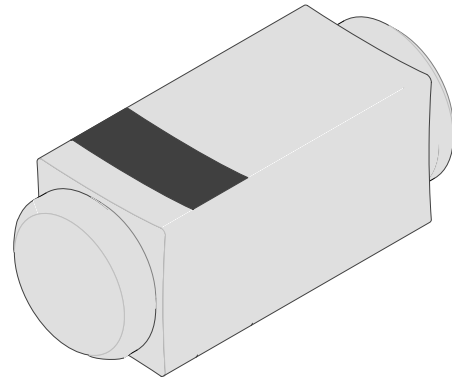
## Silicon Epitaxial Planar Diode

### Features

- Electrical data identical with the device 1N4151
- Quadro Melf package

### Applications

Extreme fast switches



94 9373

### Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage			$V_{RRM}$	75	V
Reverse voltage			$V_R$	50	V
Peak forward surge current	$t_p=1\mu\text{s}$		$I_{FSM}$	2	A
Repetitive peak forward current			$I_{FRM}$	450	mA
Forward current			$I_F$	200	mA
Average forward current	$V_R=0$		$I_{FAV}$	150	mA
Power dissipation			$P_V$	500	mW
Junction temperature			$T_j$	175	$^\circ\text{C}$
Storage temperature range			$T_{stg}$	-65...+175	$^\circ\text{C}$

### Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mmx50mmx1.6mm	$R_{thJA}$	500	K/W

## Characteristics

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=50\text{mA}$		$V_F$		0.88	1	V
Reverse voltage	$V_R=50\text{V}$		$I_R$			50	nA
	$V_R=50\text{V}, T_j=150^\circ\text{C}$		$I_R$			50	$\mu\text{A}$
Breakdown voltage	$I_R=5\mu\text{A}, t_p/T=0.01,$ $t_p=0.3\text{ms}$		$V_{(BR)}$	75			V
Diode capacitance	$V_R=0, f=1\text{ MHz},$ $V_{HF}=50\text{mV}$		$C_D$			2	pF
Reverse recovery time	$I_F=I_R=10\text{mA}, i_R=1\text{mA}$		$t_{rr}$			4	ns
	$I_F=10\text{mA}, V_R=6\text{V},$ $i_R=0.1 \times I_R, R_L=100\Omega$		$t_{rr}$			2	ns

## Typical Characteristics ( $T_j = 25^\circ\text{C}$ unless otherwise specified)

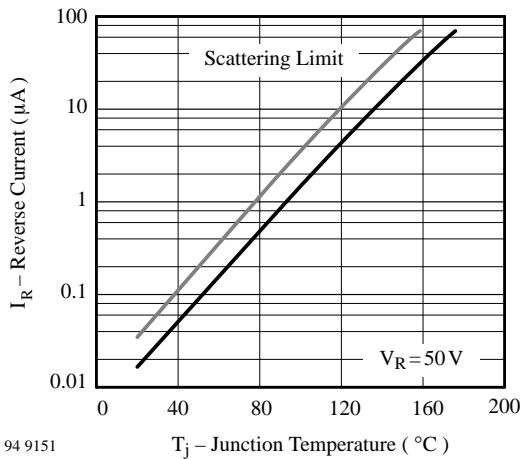


Figure 1 : Reverse Current vs. Junction Temperature

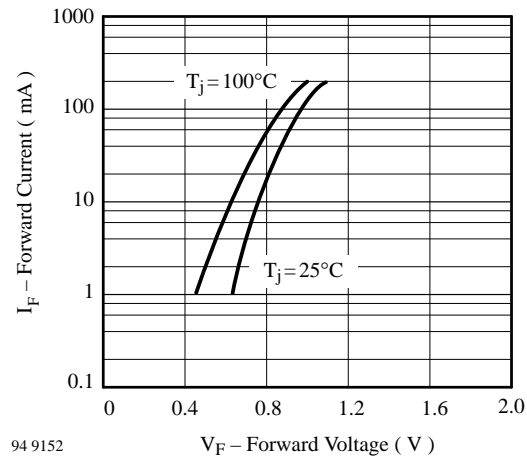


Figure 2 : Forward Current vs. Forward Voltage

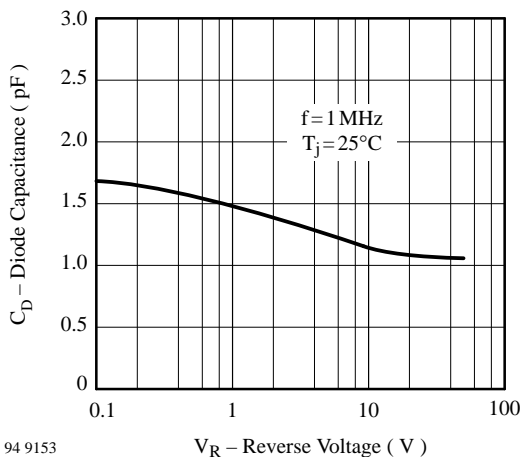
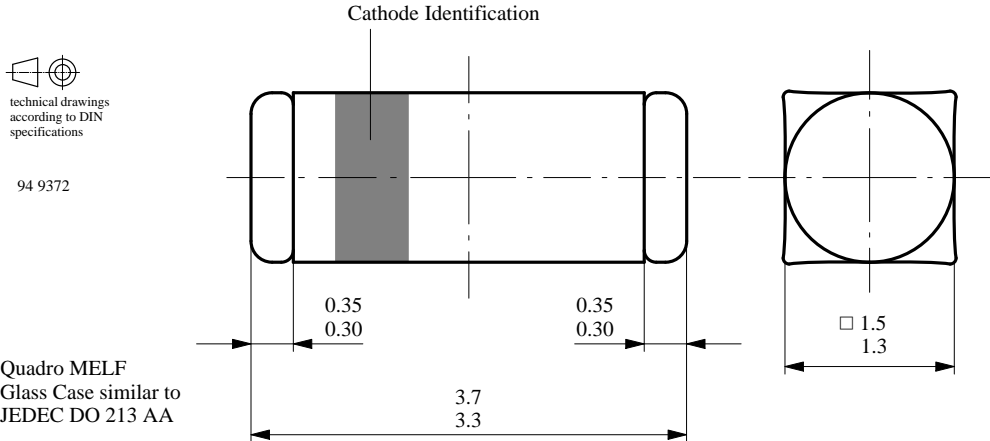


Figure 3 : Diode Capacitance vs. Reverse Voltage

## Dimensions in mm



**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements and
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

Of particular concern is the control or elimination of releases into the atmosphere of those substances which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) will soon severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of any ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA and
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with and do not contain ozone depleting substances.

**We reserve the right to make changes to improve technical design without further notice.**

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